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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	83
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg980f512-qfp100

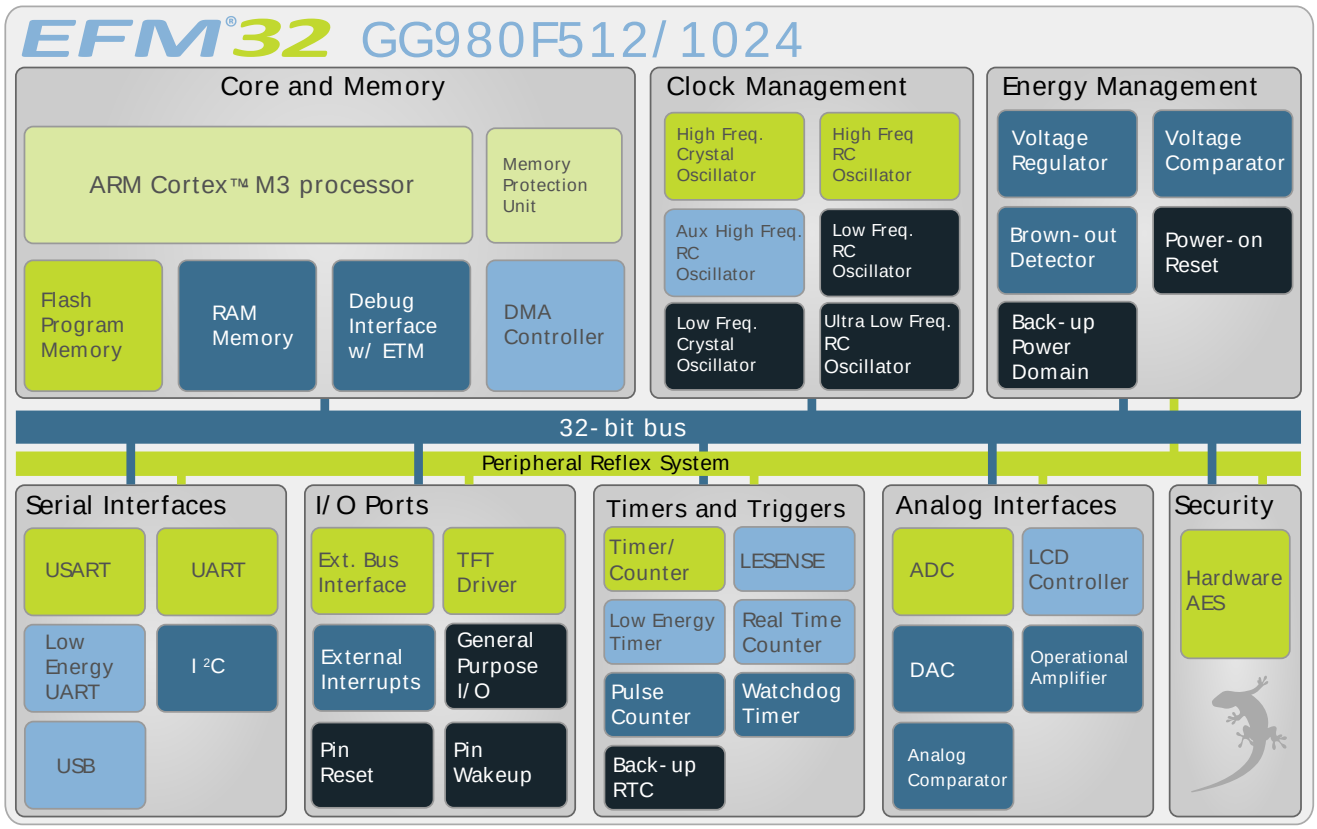
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32GG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32GG980 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32GG Reference Manual*.

A block diagram of the EFM32GG980 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing . In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10) , unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
$V_{BODintthr-}$	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85	1.98	V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF
C_{USB_VREGO}	USB voltage regulator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		µF
C_{USB_VREGI}	USB voltage regulator in decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		µF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time	LPERASE == 0	20	20.4	20.8	ms
		LPERASE == 1	40	40.4	40.8	ms
t_{DERASE}	Device erase time				161.6	ms
I_{ERASE}	Erase current	LPERASE == 0			14[1]	mA
		LPERASE == 1			7[1]	mA
I_{WRITE}	Write current	LPWRITE == 0			14[1]	mA
		LPWRITE == 1			7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

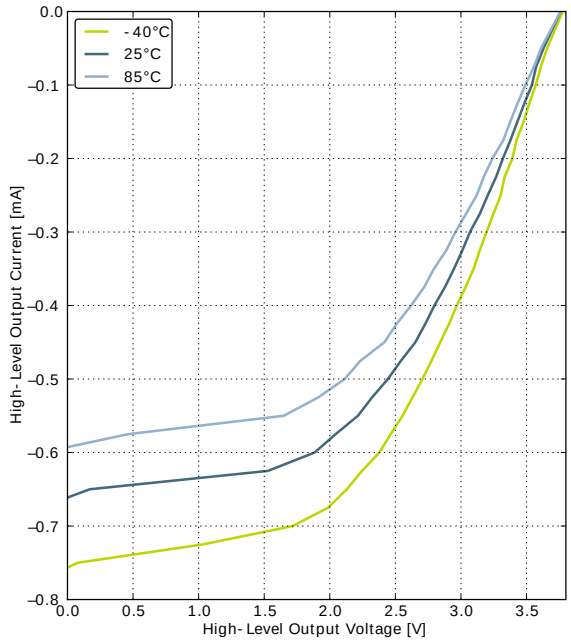
[1]Measured at 25°C

3.8 General Purpose Input Output

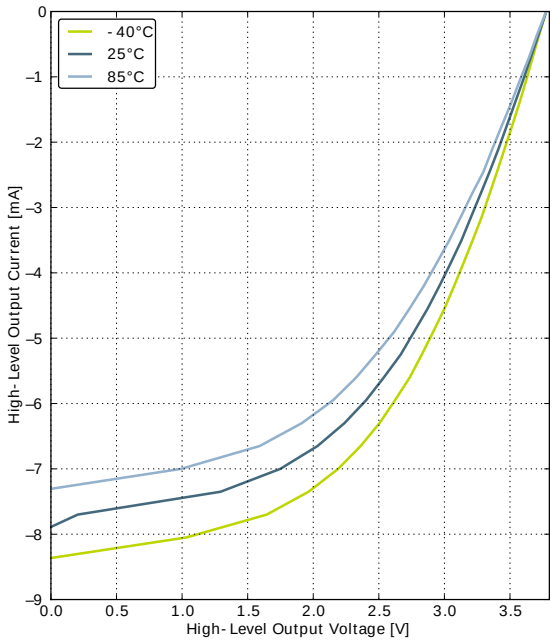
Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V

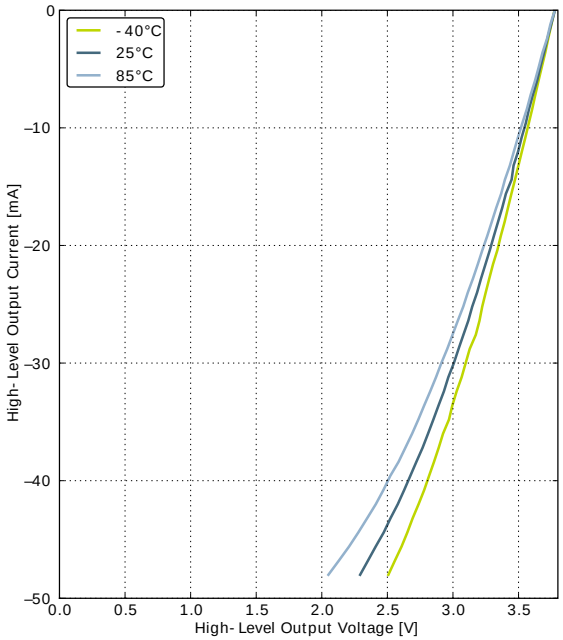
Figure 3.9. Typical High-Level Output Current, 3.8V Supply Voltage



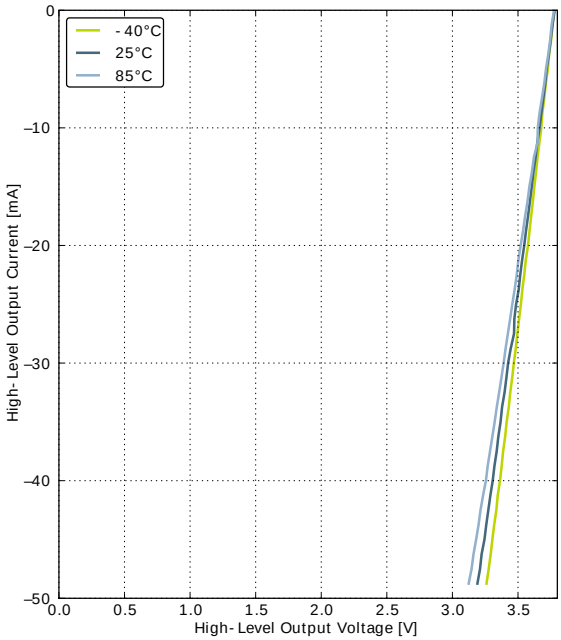
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{HFRCO}	Current consumption (Production test condition = 14MHz)	f_{HFRCO} = 28 MHz		165	190	µA
		f_{HFRCO} = 21 MHz		134	155	µA
		f_{HFRCO} = 14 MHz		106	120	µA
		f_{HFRCO} = 11 MHz		94	110	µA
		f_{HFRCO} = 6.6 MHz		77	90	µA
		f_{HFRCO} = 1.2 MHz		25	32	µA
$TUNESTEP_{H-FRCO}$	Frequency step for LSB change in TUNING value			0.3[3]		%

[1]For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

[2]For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

[3]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

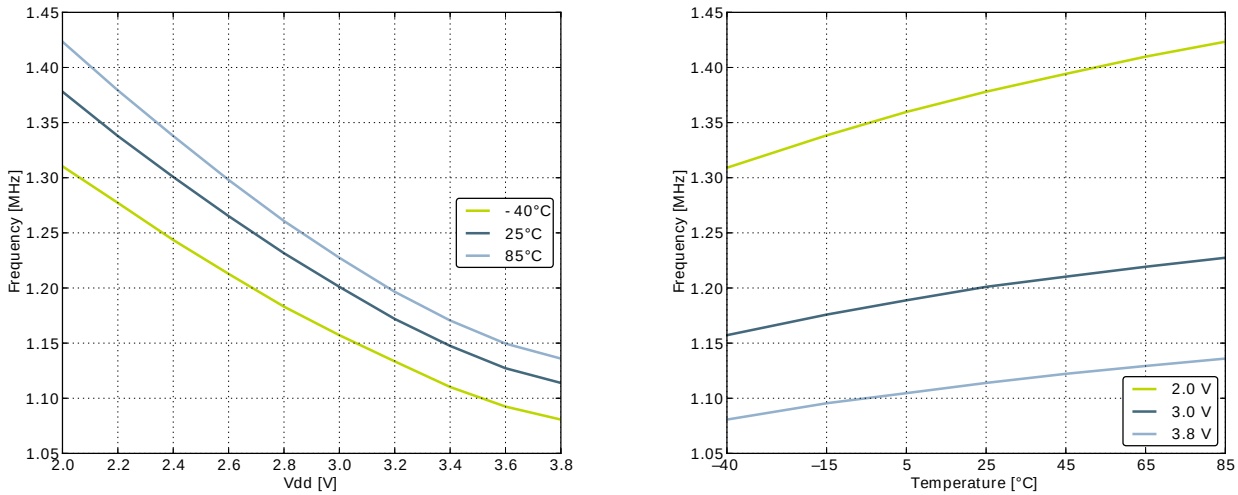


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

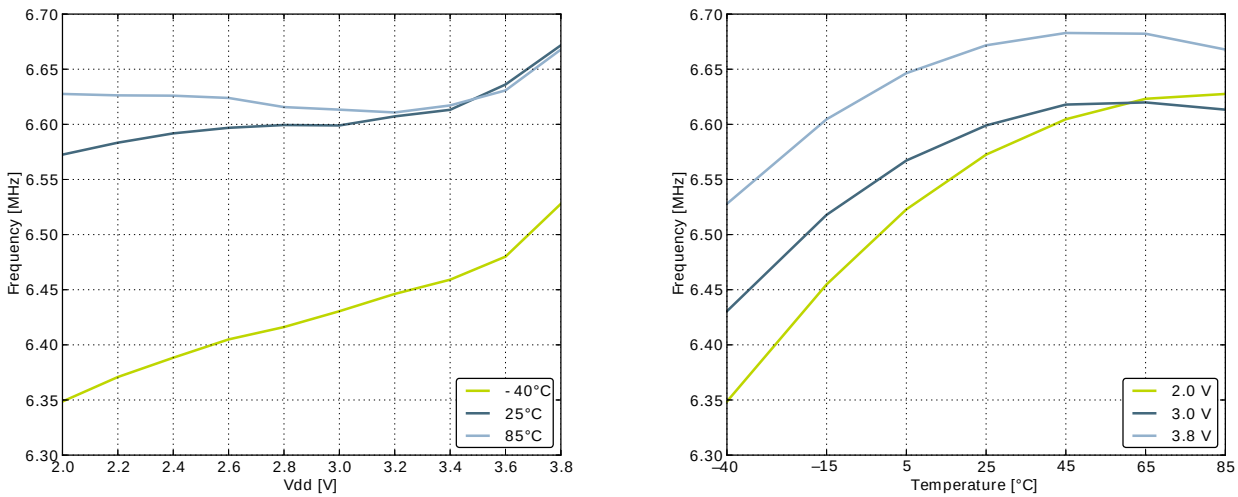


Figure 3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

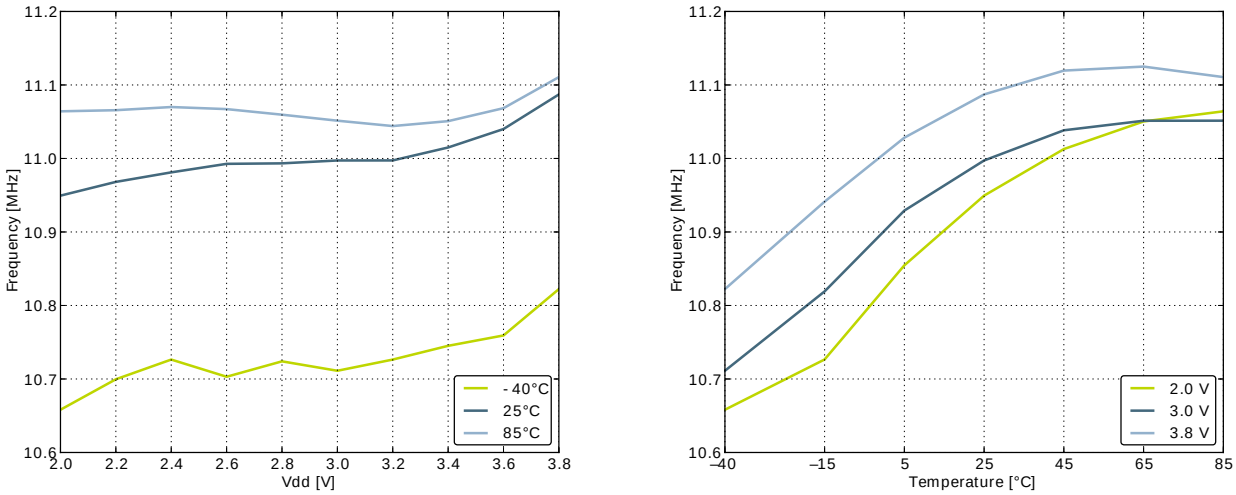


Figure 3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

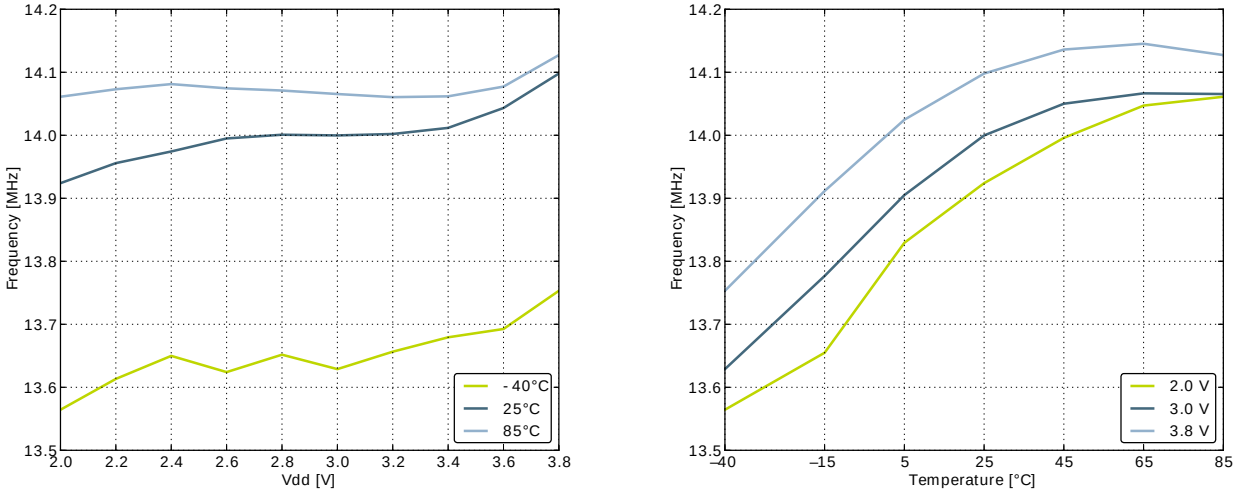
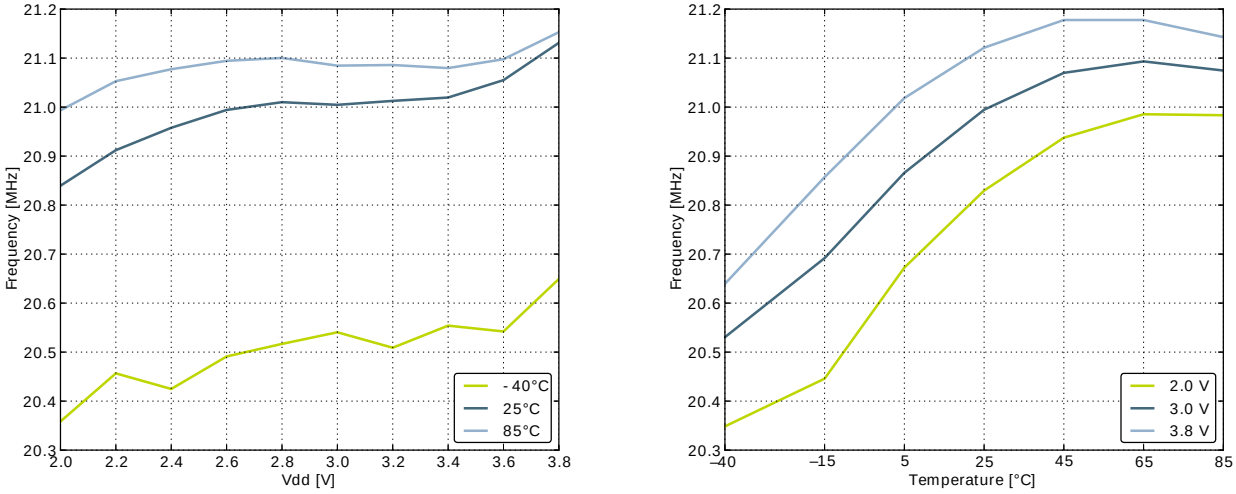
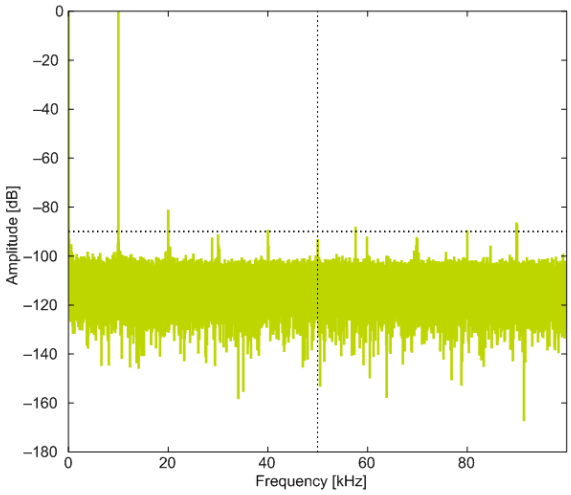


Figure 3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

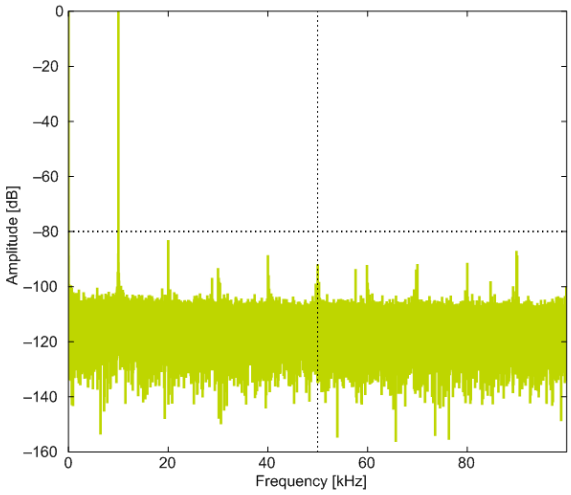


3.10.1 Typical performance

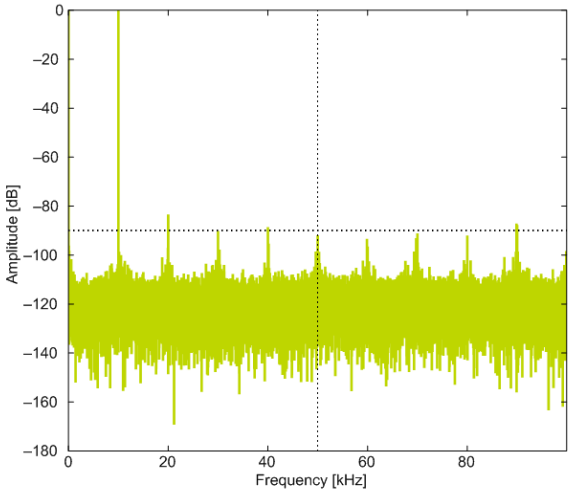
Figure 3.19. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



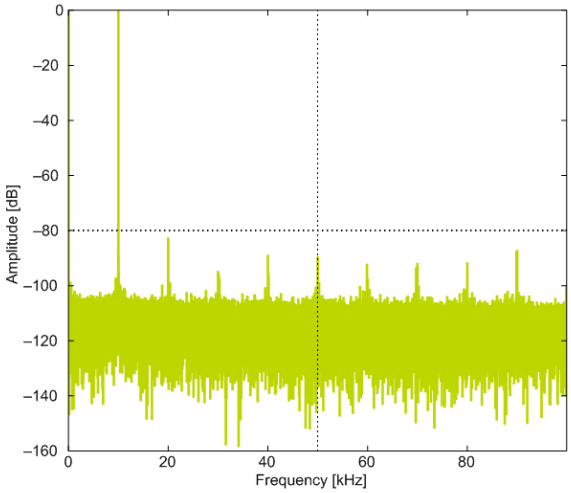
1.25V Reference



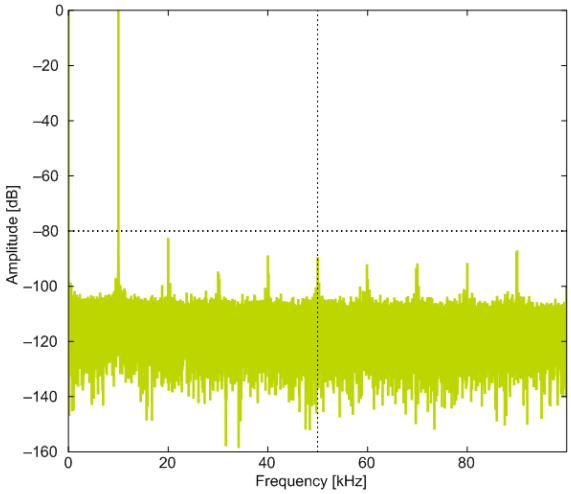
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		2590		μV_{RMS}

Figure 3.25. OPAMP Common Mode Rejection Ratio

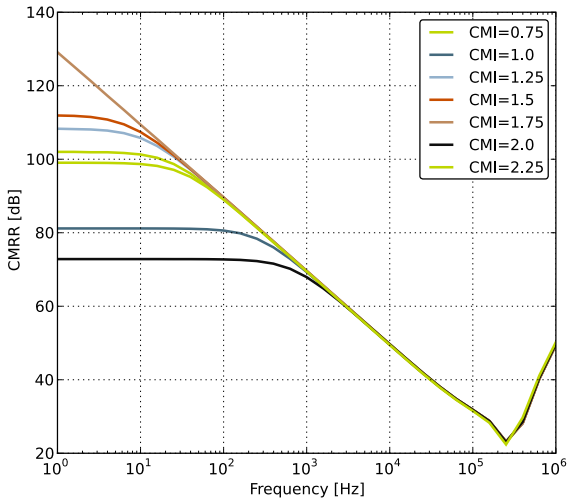


Figure 3.26. OPAMP Positive Power Supply Rejection Ratio

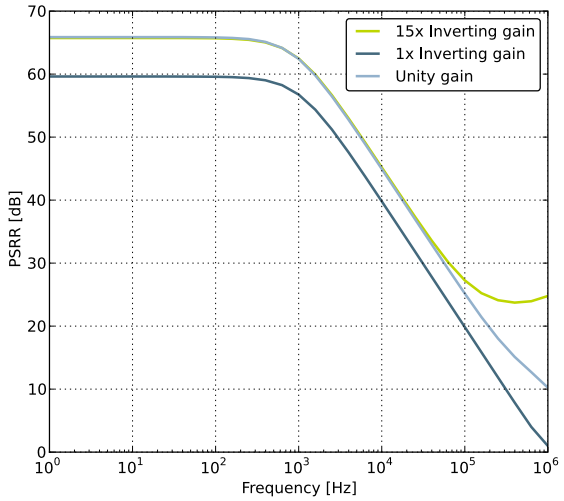
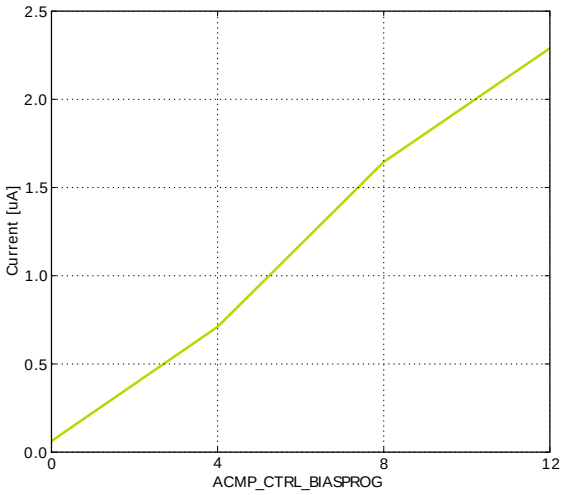
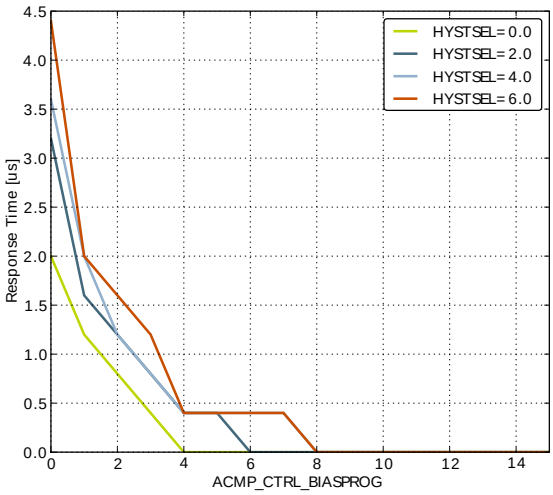


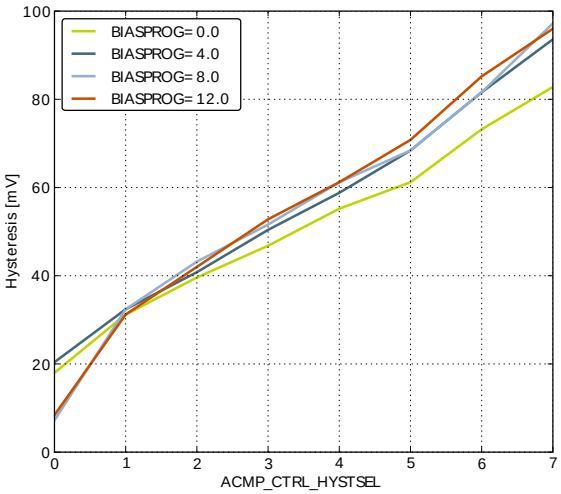
Figure 3.30. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

Table 3.19. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_WEn} [1 2 3 4]	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-6.00 + (WRHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_WEn} [1 2 3 4 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	-14.00 + (WRSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_WEn} [1 2 3 4 5]	EBI_WEn/EBI_NANDWEn pulse width	-7.00 + ((WRSTRB +1) * $t_{HFCORECLK}$)			ns

[1]Applies for all addressing modes (figure only shows D16 addressing mode)
[2]Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by 1/2 * $t_{HFCLKNODIV}$.

Figure 3.32. EBI Address Latch Enable Related Output Timing

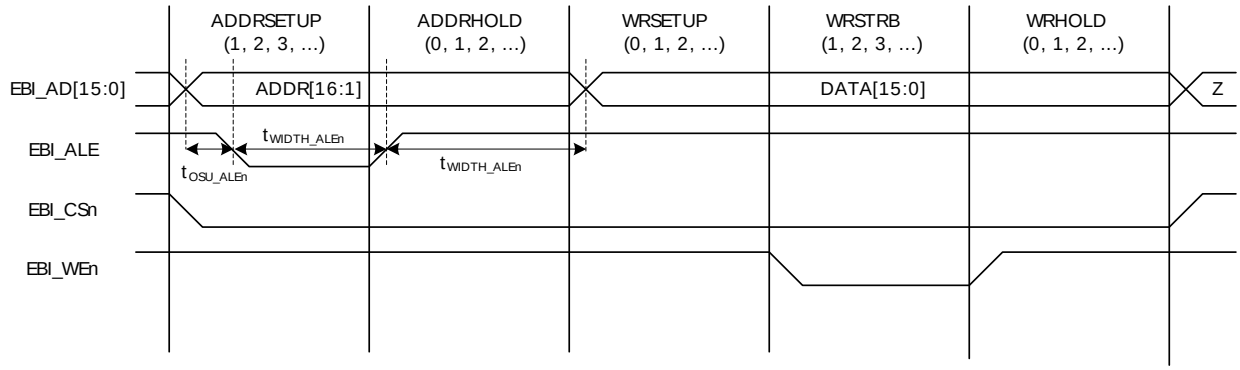


Table 3.20. EBI Address Latch Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_ALEn} [1 2 3 4]	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	-6.00 + (ADDRHOLD[5] * $t_{HFCORECLK}$)			ns
t_{OSU_ALEn} [1 2 4]	Output setup time, from EBI_AD valid to leading EBI_ALE edge	-13.00 + (0 * $t_{HFCORECLK}$)			ns
t_{WIDTH_ALEn} [1 2 3 4]	EBI_ALEn pulse width	-7.00 + (ADDRSETUP+1) * $t_{HFCORECLK}$)			ns

[1]Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)
[2]Applies for all polarities (figure only shows active low signals)
[3] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of tOH_ALEn by $t_{HFCORECLK}$ - 1/2 * $t_{HFCLKNODIV}$.
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5]Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

3.17 I2C

Table 3.25. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and START condition	4.7			µs

[1]For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32GG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < (($3450*10^{-9}$ [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.26. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and START condition	1.3			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32GG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < (($900*10^{-9}$ [s] * $f_{HFPERCLK}$ [Hz]) - 4).

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32GG980.

4.1 Pinout

The *EFM32GG980* pinout is shown in Figure 4.1 (p. 54) and Table 4.1 (p. 54). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32GG980 Pinout (top view, not to scale)

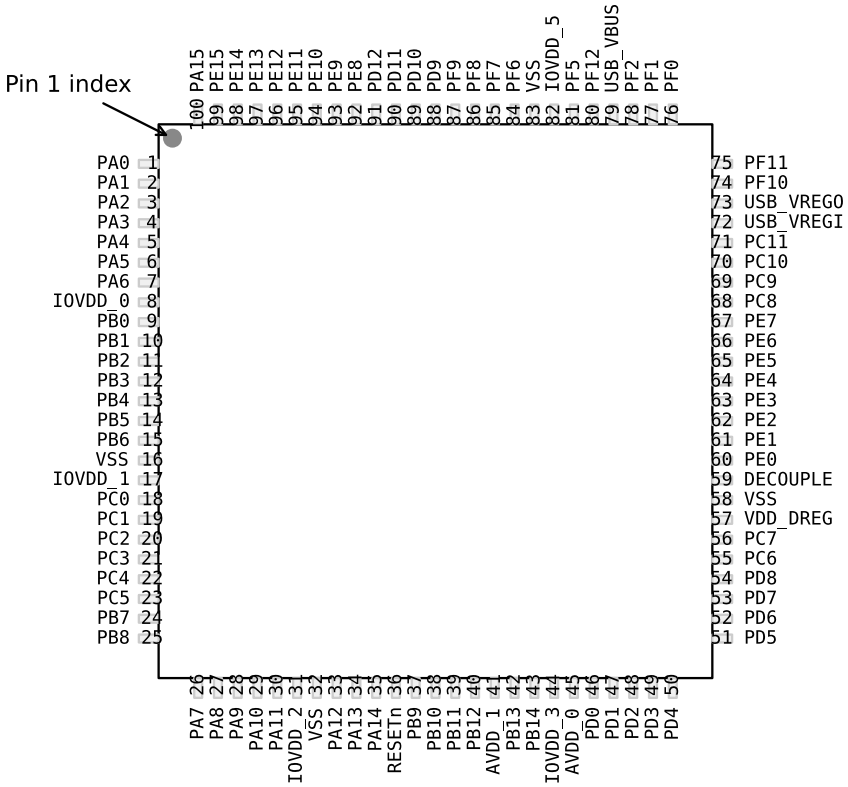


Table 4.1. Device Pinout

LQFP100 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
1	PA0	LCD_SEG13	EBI_AD09 #0/1/2	TIM0_CC0 #0/1/4	I2C0_SDA #0 LEU0_RX #4	PRS_CH0 #0 GPIO_EM4WU0
2	PA1	LCD_SEG14	EBI_AD10 #0/1/2	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0
3	PA2	LCD_SEG15	EBI_AD11 #0/1/2	TIM0_CC2 #0/1		CMU_CLK0 #0

LQFP100 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
60	PE0		EBI_A07 #0/1/2	TIM3_CC0 #1 PCNT0_S0IN #1	U0_TX #1 I2C1_SDA #2	
61	PE1		EBI_A08 #0/1/2	TIM3_CC1 #1 PCNT0_S1IN #1	U0_RX #1 I2C1_SCL #2	
62	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
63	PE3	BU_STAT	EBI_A10 #0		U1_RX #3	ACMP1_O #1
64	PE4	LCD_COM0	EBI_A11 #0/1/2		US0_CS #1	
65	PE5	LCD_COM1	EBI_A12 #0/1/2		US0_CLK #1	
66	PE6	LCD_COM2	EBI_A13 #0/1/2		US0_RX #1	
67	PE7	LCD_COM3	EBI_A14 #0/1/2		US0_TX #1	
68	PC8	ACMP1_CH0	EBI_A15 #0/1/2	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
69	PC9	ACMP1_CH1	EBI_A09 #1/2	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
70	PC10	ACMP1_CH2	EBI_A10 #1/2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
71	PC11	ACMP1_CH3	EBI_ALE #1/2		US0_TX #2	LES_CH11 #0
72	USB_VREGI					
73	USB_VREGO					
74	PF10				U1_TX #1 USB_DM	
75	PF11				U1_RX #1 USB_DP	
76	PF0			TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 I2C0_SDA #5 LEU0_TX #3	DBG_SWCLK #0/1/2/3
77	PF1			TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 I2C0_SCL #5 LEU0_RX #3	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
78	PF2	LCD_SEG0	EBI_ARDY #0/1/2	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
79	USB_VBUS	USB 5.0 V VBUS input.				
80	PF12				USB_ID	
81	PF5	LCD_SEG3	EBI_REn #0/2	TIM0_CDTI2 #2/5	USB_VBUSEN #0	PRS_CH2 #1
82	IOVDD_5	Digital IO power supply 5.				
83	VSS	Ground.				
84	PF6	LCD_SEG24	EBI_BL0 #0/1/2	TIM0_CC0 #2	U0_TX #0	
85	PF7	LCD_SEG25	EBI_BL1 #0/1/2	TIM0_CC1 #2	U0_RX #0	
86	PF8	LCD_SEG26	EBI_WEn #1	TIM0_CC2 #2		ETM_TCLK #1
87	PF9	LCD_SEG27	EBI_REn #1			ETM_TD0 #1
88	PD9	LCD_SEG28	EBI_CS0 #0/1/2			
89	PD10	LCD_SEG29	EBI_CS1 #0/1/2			
90	PD11	LCD_SEG30	EBI_CS2 #0/1/2			
91	PD12	LCD_SEG31	EBI_CS3 #0/1/2			
92	PE8	LCD_SEG4	EBI_AD00 #0/1/2	PCNT2_S0IN #1		PRS_CH3 #1
93	PE9	LCD_SEG5	EBI_AD01 #0/1/2	PCNT2_S1IN #1		

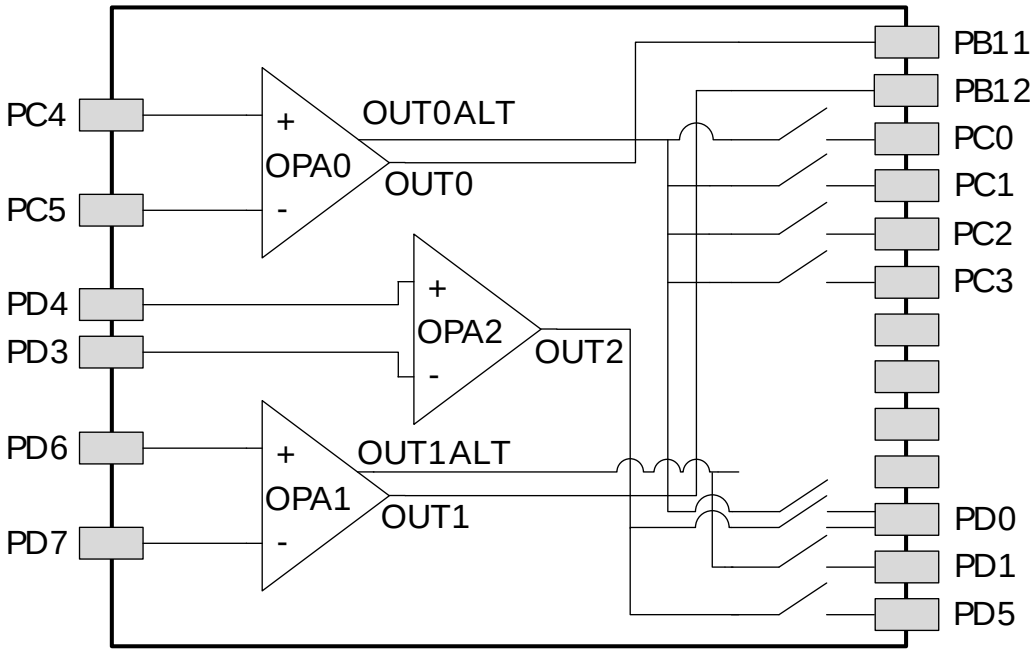
Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	PA14	PA13	PA12	PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	PB10	PB9	PB8	PB7	PB6	PB5	PB4	PB3	PB2	PB1	PB0
Port C	-	-	-	-	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	PD12	PD11	PD10	PD9	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	PE7	PE6	PE5	PE4	PE3	PE2	PE1	PE0
Port F	-	-	-	PF12	PF11	PF10	PF9	PF8	PF7	PF6	PF5	-	-	PF2	PF1	PF0

4.4 Opamp Pinout Overview

The specific opamp terminals available in *EFM32GG980* is shown in Figure 4.2 (p. 66) .

Figure 4.2. Opamp Pinout



Updated GPIO information.

Updated LFRCO information.

Updated HFRCO information.

Updated ULFRCO information.

Updated ADC information.

Updated DAC information.

Updated OPAMP information.

Updated ACMP information.

Updated VCMP information.

Added AUXHFRCO information.

7.3 Revision 1.21

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.20

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Added EBI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Added the USB bootloader information.

Updated that the EM2 current consumption test was carried out with only one RAM block enabled.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.10

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected LQFP100 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

Added reference to errata document.

Corrected LQFP100 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.10 Revision 0.91

March 21th, 2011

Added new alternative locations for EBI and SWO.

Added new USB Pin to pinout table.

Corrected slew rate data for Opamps.

7.11 Revision 0.90

February 4th, 2011

Initial preliminary release.

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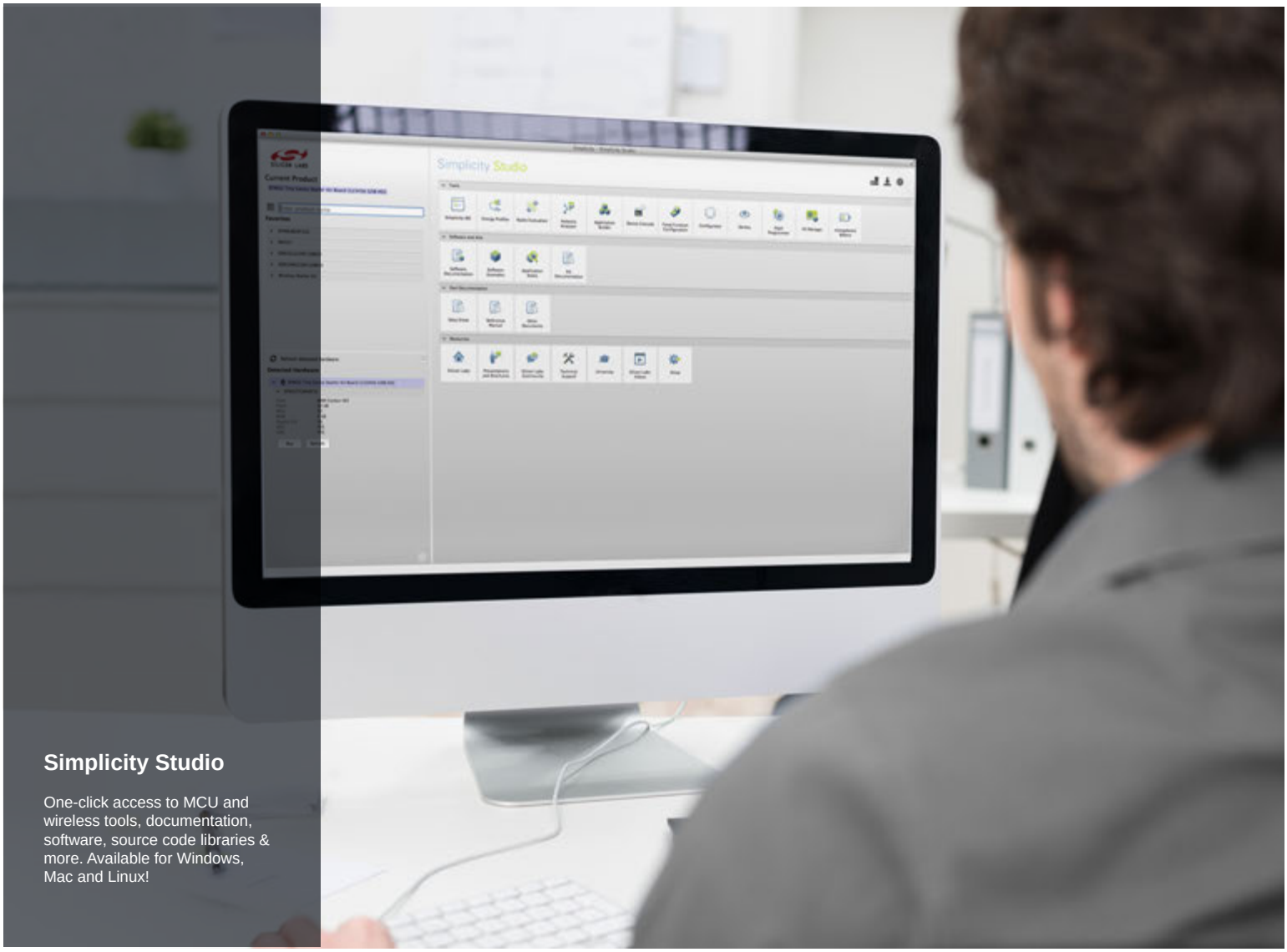

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